process similarly as described in Example 3 using the compositions of preliminary and main plating bath under the plating conditions as shown in Tables 3 and 4 in Example 7, respectively, which was then cut off in a similar manner as described in Example 7 to form chip parts having a shape of Fig. 9 (perspective view).

Example 9

The base assembly 21 used in Example 7 was partially coated with coating material 3 as shown in Fig. 7 (A) to (C) and subjected to a plating process similarly as described in Example 4 using the compositions of preliminary and main plating bath under the plating conditions as shown in Tables 3 and 4 in Example 7, respectively, which was then cut off in a similar manner as described in Example 7 to form chip parts having a shape of Fig. 9 (perspective view).

Example 10

The base assembly 21 used in Example 7 was partially coated with coating material 3 as shown in Fig. 7 (A) to (C) and subjected to a plating process similarly as described in Example 5 using the compositions of preliminary and main plating bath under the plating conditions as shown in Tables 3 and 4 in Example 7, respectively, which was then cut off in a similar manner as described in Example 7 to form chip parts having a shape of Fig. 9 (perspective view).

Example 11

A procedure of Example 9 was repeated except that the assembly 21 was coated with PVA as a coating material and plated by treating thereof with aluminum chloride and lithium hydroxide in a tetrahydrofurn solution to form a Al-plated layer of 2μ m thick (generally 0.5 to 2.5μ m thick) thereon.